Claims

1. A method for depositing an epitaxial layer on a substrate wafer from a vapor phase, comprising
measuring an edge geometry of the substrate wafer that assigns a thickness characteristic value to an edge of the substrate wafer as a function of edge positions, the substrate wafer having a thicker edge section and a thinner edge section which are opposite each other;
placing the substrate wafer in a pocket of a susceptor of a device for depositing the epitaxial layer, the pocket being surrounded by a boundary with a circular circumference;
heating the substrate wafer; and
passing process gas over the substrate wafer;
characterized by
placing the substrate wafer in the pocket such that the distance from the substrate wafer to the boundary of the pocket is smaller at edge positions of the thicker edge section with greater thickness characteristic value than at edge positions of the thinner edge section with smaller thickness characteristic value.

2. The method as claimed in claim 1, characterized by measuring the ESFQR or the ZDD as the thickness characteristic value.

3. The method as claimed in any of claims 1 to 2, characterized by
placing the substrate wafer by means of a robot.

4. The method as claimed in any of claims 1 to 3, characterized by
monitoring the position of the substrate wafer in the pocket by means of a camera system.

5. The method as claimed in any of claims 1 to 4, characterized by
depositing an epitaxial layer of silicon on a single-crystal silicon wafer.